



P A T E N T

Attorney Docket No.  
033035 M 0342

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of: ) CONFIRMATION NO.: 6958  
Kensaku MOTOKI, et al. )  
U.S. Serial No.: 10/691,569 ) Group Art Unit: 2814  
Filed: October 24, 2003 ) Examiner: Marcos D. Pizarro Crespo

For: GaN SINGLE CRYSTAL SUBSTRATE AND METHOD OF MAKING THE SAME

Sir:

**FIFTH INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure under 37 C.F.R. 1.56, Applicants enclose an Information Disclosure Citation Form (PTO-1449) and a copy of the documents cited therein. The documents were cited by the Examiner in another Office Action issued for copending Application No. 10/691,540.

It is respectfully requested that the cited documents be considered by the Examiner, that they be made officially of record therein, and that the documents be listed on the face of any patent which may issue from this application. This paper is being submitted with a Request for Continued Examination (RCE) and therefore no fees are considered necessary.

Respectfully submitted,  
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Date: July 26, 2007



FORM PTO-1449  INFORMATION DISCLOSURE STATEMENT		ATTY. DOCKET 033035 M 0342	SERIAL NO. 10/691,569
		APPLICANTS: Kensaku MOTOKI, et al.	
		FILING DATE October 24, 2003	GROUP ART UNIT 2814

#### U.S. PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE, IF APPROPRIATE
	AA	5,828,088	10/27/1998	MAUK			
	AB	5,838,029	11/17/1998	SHAKUDA			
	AC	5,679,152	10/21/1997	TISCHLER et al.			
	AD	5,182,233	01/26/1993	INOUE			
	AE	5,770,887	06/23/1998	TADATOMO et al.			
	AF						
	AG						

#### FOREIGN PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLAS S	TRANSLATION YES NO
	AH						
	AI						
	AJ						
	AK						

#### OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

	AL	Office Action for U. S. Patent Application No. 10/691,540 dated April 5, 2005.
	AM	IBM, Abstract of "Method of Producing Gallium Nitride Boules for Processing into Substrates," IBM Technical Disclosure Bulletin May 1997, Vol 40, Issue 5, May 1, 1997.
	AN	Zheleva et al. "Dislocation density reduction via lateral epitaxy in selectively grown GaN structures," Appl. Phys. Lett. 71 (17) 27 October 1997, pp 2472-2474.
	AO	Nam et al. "Lateral epitaxy of low defect density GaN layers via organometallic vapor phase epitaxy," Appl. Phys. Lett. 71 (18), 3 November 1997, pp. 2638-2640.
	AP	
	AQ	

EXAMINER:	DATE CONSIDERED:
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.